

FEATURES

■ **HIGH POWER**

P1dB=37.0dBm at 12.7GHz to 13.2GHz

■ **BROAD BAND INTERNALLY MATCHED**

■ **HERMETICALLY SEALED PACKAGE**

■ **HIGH GAIN**

G1dB=7.0dB at 12.7GHz to 13.2GHz

RF PERFORMANCE SPECIFICATIONS (Ta= 25° C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Compression Point	P1dB	VDS= 9V f= 12.7 to 13.2GHz	dBm	37.0	37.5	—
Power Gain at 1dB Compression Point	G1dB		dB	6.0	7.0	—
Drain Current	IDS1		A	—	2.0	2.5
Power Added Efficiency	η_{add}		%	—	25	—
Channel Temperature Rise	ΔT_{ch}		VDS X IDS X Rth(c-c)	°C	—	—

ELECTRICAL CHARACTERISTICS (Ta= 25° C)

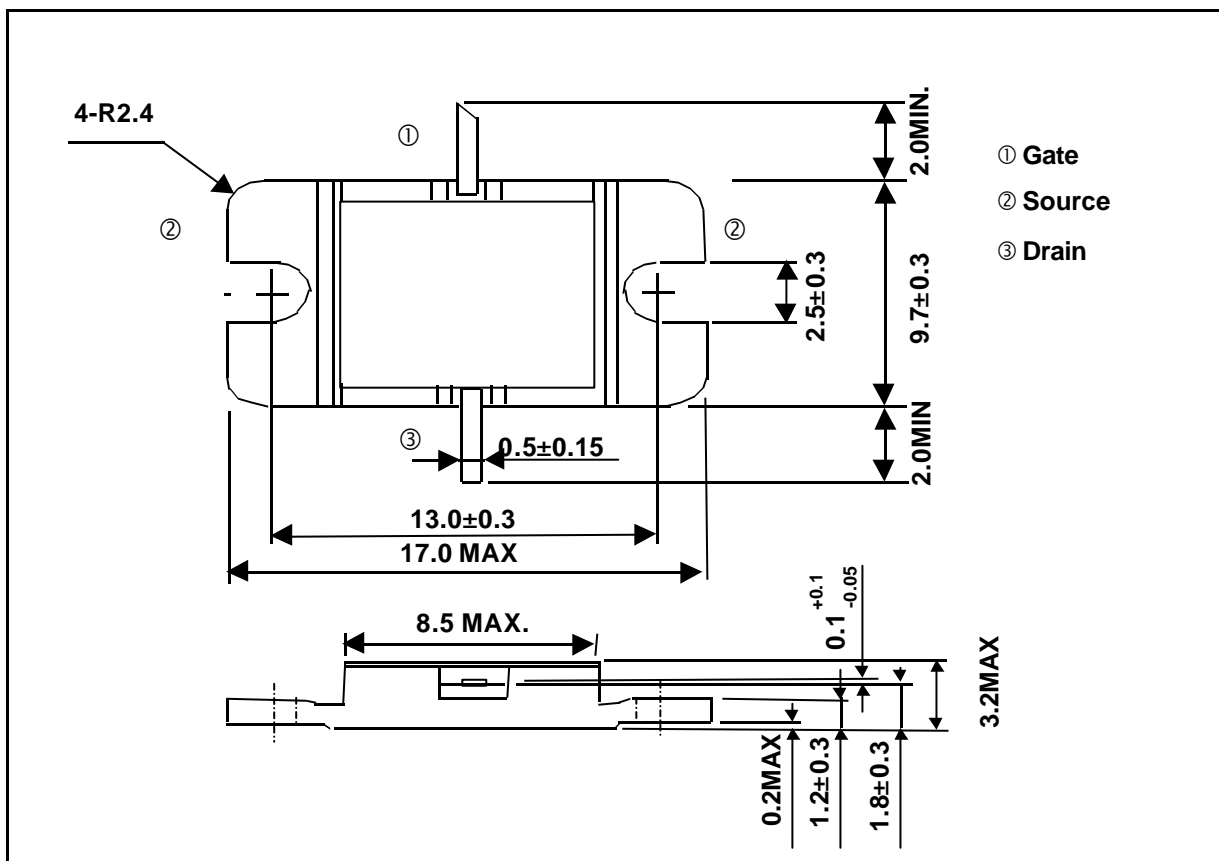
CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 2.4A	mS	—	1400	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 72mA	V	-2.0	-3.5	-5.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	5.0	5.7
Gate-Source Breakdown Voltage	VGSO	IGS= -72 μ A	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	3.0	3.7

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ABSOLUTE MAXIMUM RATINGS (Ta= 25° C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	5.7
Total Power Dissipation (Tc= 25 °C)	PT	W	30
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-9D1B)**HANDLING PRECAUTIONS FOR PACKAGED TYPE**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.